TOSHIBA THYRISITOR SILICON PLANAR TYPE

RSF05G1-1P,RSF05G1-3P,RSF05G1-5P

LOW POWER SWITCHING AND CONTROL APPLICATIONS

• Repetitive Peak Off–State Voltage $: V_{DRM} = 400V$ Repetitive Peak Reverse Voltage $V_{RRM} = 400V$ • Average On-State Current $I_{T(AV)} = 500 \text{mA}$

• Plastic Mold Type

Reduce a Quantity of Parts and Manufacturing

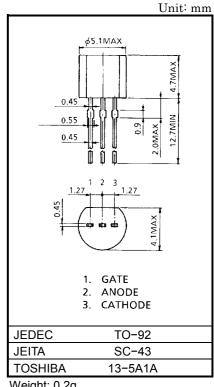
Process Because of Built-in RGK : RGK = $1k\Omega$, $2.7k\Omega$, $5.1k\Omega$

(Typical)

MAXIMUM RATINGS

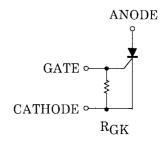
CHARACTERISTIC		SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	RSF05G1-1P		400		
	RSF05G1-3P	V _{DRM} V _{RRM}	400	V	
	RSF05G1-5P		400		
Non-Repetitive Peak Reverse Voltage (Non-Repetitive< 5ms, Tj = 0~125°C)	RSF05G1-1P		500		
	RSF05G1-3P	V_{DSM}	500	V	
	RSF05G1-5P		500		
Average On-State Current (Half Sine Waveform)		I _{T(AV)}	500	mA	
R.M.S. On-State Current		I _{T(RMS)}	800	mA	
Peak One Cycle Surge On-State Current (Non-Repetitive)		l=	9 (50Hz)	А	
		ITSM	10 (60Hz)		
I ² t Limit Value		I ² t	0.4	A ² s	
Critical Rate of Rise of On-State Current		di / dt	10	A/μs	
Peak Gate Power Dissipation		P_{GM}	0.1	W	
Average Gate Power Dissipation		$P_{G(AV)}$	0.01	W	
Peak Forward Gate Voltage		V_{FGM}	3.5	V	
Peak Reverse Gate Voltage		V_{RGM}	-5	V	
Peak Forward Gate Current		I _{GM}	125	mA	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature		T _{stg}	-40~125	°C	

di / dt Test Condition, i_G = 5mA, t_{gw} = 10 μ s, $t_{gr} \le$ 250ns



Weight: 0.2g

EQUIVALENT CIRCUIT



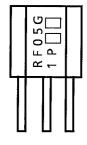


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT	
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current		I _{DRM} I _{RRM}	V _{DRM} = V _{RRM} = Rated	_	_	10	μA	
Peak On-State Voltage		V _{TM}	I _{TM} = 1A	_	_	1.5	V	
Gate Trigger Voltage		V _{GT}		0.4	_	0.8	V	
Gate Trigger Current	RSF05G1-1P			400	700	1000		
		RSF05G1-3P	I _{GT}	$V_D = 6V, R_L = 100\Omega$	150	250	400	μΑ
		RSF05G1-5P			80	160	250	
Holding Current		RSF05G1-1P			_	_	6	
	RSF05G1-3P	lн	$I_{TM} = 1A$, $V_D = 6V$	_	_	3	mA	
	RSF05G1-5P			_	_	2		
Resistor Between Gate and Cathode		RSF05G1-1P			700	1000	1300	
	RSF05G1-3P	R _{GK}	_	1890	2700	3510	Ω	
	RSF05G1-5P			3570	5100	6630		
Critical Rate of Rise of Off-State Voltage	of	RSF05G1-1P	dv / dt	V _{DRM} = Rated Exponential Rise	_	200	_	V / µs
		RSF05G1-3P			_	70	_	
		RSF05G1-5P			_	40	_	
Gate Turn-On Time		t _{gt}	V _D = Rated, i _G = 5mA	_	_	1.5	μs	
Posistanas	Junction to Lead		R _{th(j −ℓ)}	- DC	_	_	40	°C/W
	Junction to Ambient		R _{th(j-a)}		_	_	180	

MARKING

Example : It is mark of RSF05G1-1P



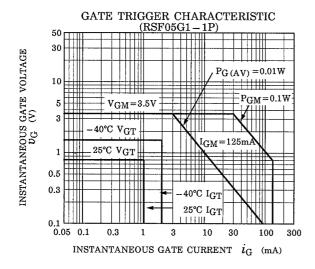
Lot Number

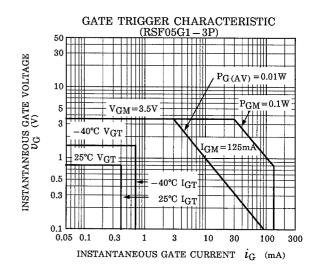
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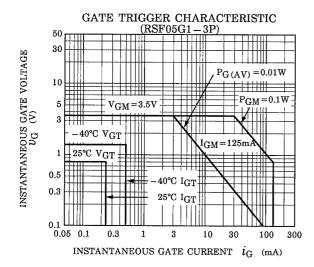
Example 8A: January 1998

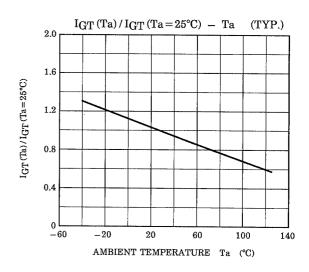
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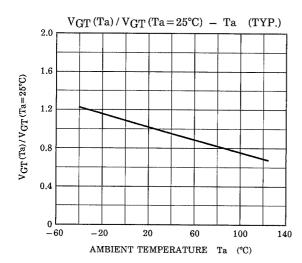
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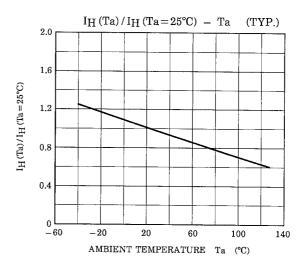


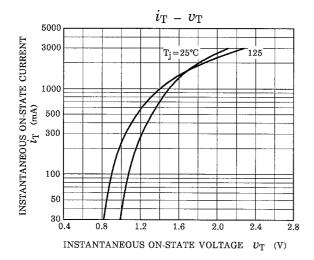


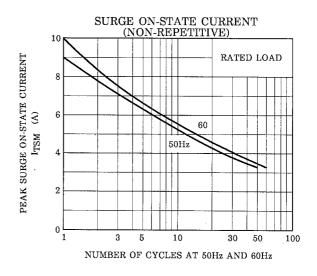


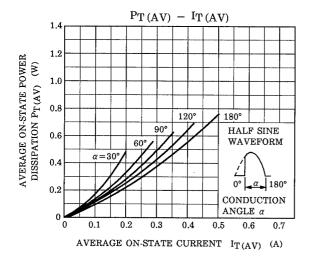


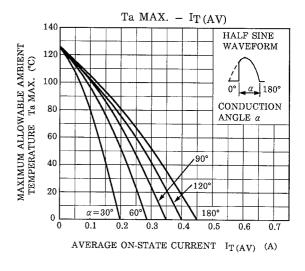


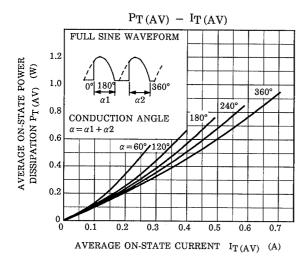


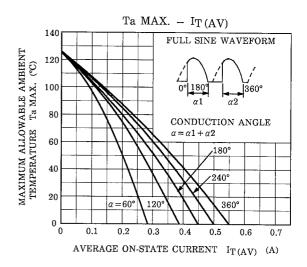




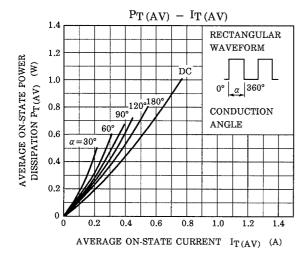


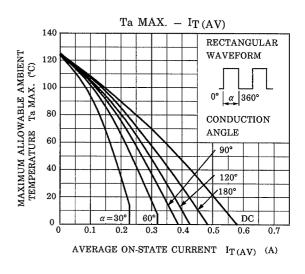


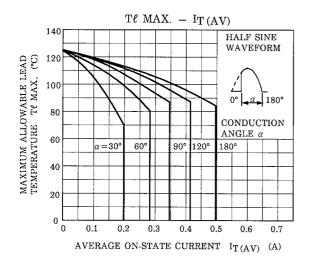


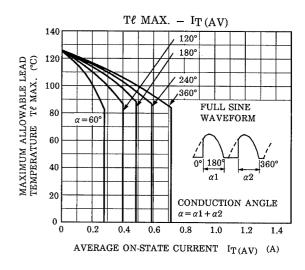


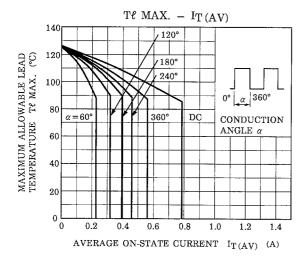
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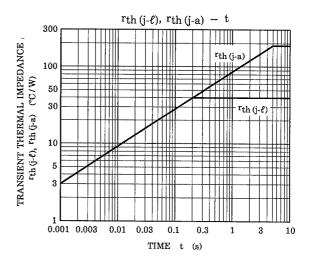












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